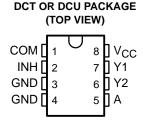
SN74LVC2G53 DUAL ANALOG MULTIPLEXER/DEMULTIPLEXER

SCES324I - JULY 2001 - REVISED FEBRUARY 2003

- Available in the Texas Instruments NanoStar™ and NanoFree™ Packages
- 1.65-V to 5.5-V V_{CC} Operation
- **High On-Off Output Voltage Ratio**
- **High Degree of Linearity**
- High Speed, Typically 0.5 ns ($V_{CC} = 3 \text{ V}$, $C_L = 50 pF$
- Low On-State Resistance, Typically \approx 6.5 Ω $(V_{CC} = 4.5 \text{ V})$
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22**
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)



YEA, YEP, YZA, OR YZP PACKAGE (BOTTOM VIEW)

GND	O 4	50	Α
GND	○3	60	Y2
INH	O 2	70	Y1
GND GND INH COM	O 1	80	Vcc

description/ordering information

This dual analog multiplexer/demultiplexer is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G53 can handle both analog and digital signals. The device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

ORDERING INFORMATION

TA	PACKAGE [†]	PACKAGET		
	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA		SN74LVC2G53YEAR	
	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)	Reel of 3000	SN74LVC2G53YZAR	C4
-40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Reel of 3000	SN74LVC2G53YEPR	04_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G53YZPR	
	SSOP - DCT	Reel of 3000	SN74LVC2G53DCTR	C53
	VSSOP – DCU	Reel of 3000	SN74LVC2G53DCUR	C53
	V3301 - D00	Reel of 250	SN74LVC2G53DCUT	033_

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEA/YZA, YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

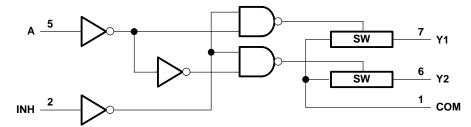
NanoStar and NanoFree are trademarks of Texas Instruments.

Copyright @ 2003, Texas Instruments Incorporated

FUNCTION TABLE

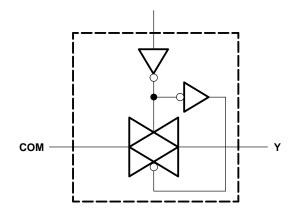
CONT	-	ON CHANNEL
INH	Α	CHANNEL
L	L	Y1
L	Н	Y2
Н	Χ	None

logic diagram (positive logic)



NOTE A: For simplicity, the test conditions shown in Figures 1 through 4 and 6 through 10 are for the demultiplexer configuration. Signals can be passed from COM to Y1 (Y2) or from Y1 (Y2) to COM.

simplified schematic, each switch (SW)





SCES324I - JULY 2001 - REVISED FEBRUARY 2003

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)		\dots -0.5 V to 6.5 V
Input voltage range, V _I (see Notes 1 and 2)		\dots -0.5 V to 6.5 V
Switch I/O voltage range, V _{I/O} (see Notes 1, 2,	and 3)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Control input clamp current, I _{IK} (V _I < 0)		
I/O port diode current, I_{IOK} ($V_{I/O} < 0$ or $V_{I/O} > V$	/ _{CC})	±50 mA
On-state switch current, $I_T (V_{I/O} = 0 \text{ to } V_{CC})$		±50 mA
Continuous current through V _{CC} or GND		±100 mA
Package thermal impedance, θ_{JA} (see Note 4):	DCT package	220°C/W
	DCU package	227°C/W
	YEA/YZA package	140°C/W
	YEP/YZP package	102°C/W
Storage temperature range, T _{Stg}		65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to ground unless otherwise specified.

- 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 3. This value is limited to 5.5 V maximum.
- 4. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 5)

			MIN	MAX	UNIT	
Vcc	Supply voltage		1.65	5.5	V	
V _{I/O}	I/O port voltage		0	Vcc	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$V_{CC} \times 0.65$			
V	High level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	$V_{CC} \times 0.7$		V	
VIH	High-level input voltage, control input	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	V _{CC} × 0.7		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	V _{CC} × 0.7			
	Low-level input voltage, control input	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		V _{CC} × 0.35	V	
\/		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		$V_{CC} \times 0.3$		
VIL		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		$V_{CC} \times 0.3$	V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$V_{CC} \times 0.3$		
٧ı	Control input voltage		0	5.5	V	
		V _{CC} = 1.65 V to 1.95 V		20		
Δt/Δν	Input transition rise #all time	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		20	no/\/	
ΔυΔν	Input transition rise/fall time	V _{CC} = 3 V to 3.6 V		10	ns/V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		10		
TA	Operating free-air temperature		-40	85	°C	

NOTE 5: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



SCES324I – JULY 2001 – REVISED FEBRUARY 2003

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			TEST CONDIT	VCC	MIN TYPT	MAX	UNIT	
				$I_S = 4 \text{ mA}$	1.65 V	13	30	
_	On state switch registeres		$V_I = V_{CC}$ or GND,	$I_S = 8 \text{ mA}$	2.3 V	10	20	Ω
r _{on}	On-state switch resistance		VINH = VIL (see Figures 1 and 2)	I _S = 24 mA	3 V	8.5	17	12
			,	I _S = 32 mA	4.5 V	6.5	13	
				$I_S = 4 \text{ mA}$	1.65 V	86.5	120	
, , ,	Peak on-state resistance		$V_I = V_{CC}$ to GND,	I _S = 8 mA	2.3 V	23	30	Ω
ron(p)	Feak Oil-state resistance		VINH = VIL (see Figures 1 and 2)	I _S = 24 mA	3 V	13	20	52
			,	$I_S = 32 \text{ mA}$	4.5 V	8	15	
				$I_S = 4 \text{ mA}$	1.65 V		7	
1	Difference of on-state resistance		$V_I = V_{CC}$ to GND,	$I_S = 8 \text{ mA}$	2.3 V		5	
∆r _{on}	between switches		VC = VIH (see Figures 1 and 2)	I _S = 24 mA	3 V		3	Ω
			,	I _S = 32 mA	4.5 V		2	
			$V_I = V_{CC}$ and $V_O = GND$ or $V_I = GND$ and $V_O = V_{CC}$, $V_{INH} = V_{IH}$ (see Figure 3)				±1	
IS(off)	Off-state switch leakage current				5.5 V		±0.1 [†]	μА
IS(on)	On-state switch leakage current		$V_I = V_{CC}$ or GND, $V_{INH} = V_{IL}$,		5.5 V		±1	μА
- (-1.)			V _O = Open (see Figure 4)				±0.1 [†]	·
l ₁	Control input current		V _C = V _{CC} or GND		5.5 V		±1	μΑ
<u> </u>							±0.1 [†]	·
l _{CC}	Supply current		$V_C = V_{CC}$ or GND		5.5 V		10	μΑ
	12						1†	
∆lcc	Supply-current change		$V_C = V_{CC} - 0.6 V$		5.5 V		500	μΑ
C _{ic}	Control input capacitance				5 V	3.5		pF
C _{io(off)}	Switch input/output capacitance	Υ			5 V	6.5		pF
~IO(OII)	2	COM			Ŭ	10		Ρ'
C _{io(on)}	Switch input/output capacitance				5 V	19.5		pF
† T∧ = 25°C								•

 $^{^{\}dagger}T_{A} = 25^{\circ}C$

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 5)

PARAMETER FROM		FROM TO ± 0.15 \(\frac{1.8}{1.00}\)			V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
	(INFO1)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ‡	COM or Y	Y or COM		2		1.2		0.8		0.6	ns
t _{en} §	INH	COM or Y	3.3	9	2.5	6.1	2.2	5.4	1.8	4.5	20
t _{dis} ¶	INF	CONTOL	3.2	10.9	2.3	8.3	2.3	8.1	1.6	8	ns
t _{en} §	Α	COMor V	2.9	10.3	2.1	7.2	1.9	5.8	1.3	5.4	no
t _{dis} ¶	A	COM or Y	2.1	9.4	1.4	7.9	1.1	7.2	1	5	ns

[‡] tpLH and tpHL are the same as tpd. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



[§] tpZL and tpZH are the same as ten.

[¶] tpLZ and tpHZ are the same as tdis.

analog switch characteristics, $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	vcc	TYP	UNIT
				1.65 V	35	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$ $f_{\text{in}} = \text{sine wave}$	2.3 V	120	
			(see Figure 6)	3 V	190	
Frequency response†	COM or Y	Y or COM	, ,	4.5 V	215	MHz
(switch on)	CONTOLL	1 OI COM		1.65 V	>300	IVII IZ
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	>300	
			f _{in} = sine wave (see Figure 6)	3 V	>300	
			,	4.5 V	>300	
				1.65 V	-58	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-58	
			f _{in} = 1 MHz (sine wave) (see Figure 7)	3 V	-58	
Crosstalk [‡]	COM or Y	V or COM	(555) (555)	4.5 V	-58	٩D
(between switches)	COM or Y	Y or COM		1.65 V	-42	dB
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	
			f _{in} = 1 MHz (sine wave) (see Figure 7)	3 V	-42	
				4.5 V	-42	
	INH	COM or Y	C_L = 50 pF, R_L = 600 Ω , f_{in} = 1 MHz (square wave) (see Figure 8)	1.65 V	35	mV
Crosstalk				2.3 V	50	
(control input to signal output)				3 V	70	
				4.5 V	100	
				1.65 V	-60	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-60	
			f _{in} = 1 MHz (sine wave) (see Figure 9)	3 V	-60	
Feed-through attenuation [‡]	2014	V 0014	(See Figure 3)	4.5 V	-60	ın
(switch off)	COM or Y	Y or COM		1.65 V	-50	dB
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-50	1
			f _{in} = 1 MHz (sine wave) (see Figure 9)	3 V	-50	
			(300 riguio 3)	4.5 V	-50	
				1.65 V	0.1	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025	
			f _{in} = 1 kHz (sine wave) (see Figure 10)	3 V	0.015	
	2014	V == 2214	(See Figure 10)	4.5 V	0.01	0.1
Sine-wave distortion	COM or Y	Y or COM		1.65 V	0.15	%
			C_L = 50 pF, R_L = 10 kΩ,	2.3 V	0.025	
			f _{in} = 10 kHz (sine wave)	3 V	0.015	
			(see Figure 10)	4.5 V	0.01	

[†] Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads –3 dB. ‡ Adjust f_{in} voltage to obtain 0 dBm at input.

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST COM	TEST CONDITIONS		V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT	
		FARAMETER	1231 001	1E31 CONDITIONS		TYP	TYP	TYP	UNIT
	C _{pd}	Power dissipation capacitance	$C_L = 50 pF$,	f = 10 MHz	9	10	10	12	pF



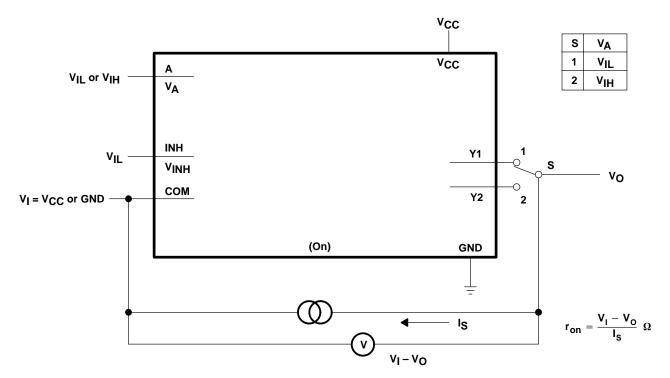


Figure 1. On-State Resistance Test Circuit

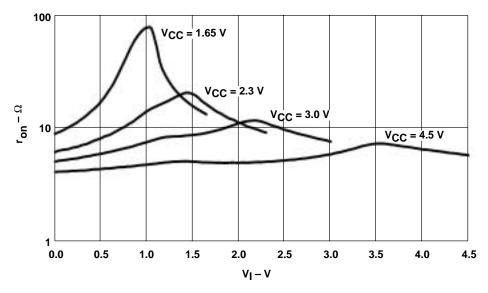


Figure 2. Typical r_{on} as a Function of Input Voltage (V_I) for $V_{I} = 0$ to V_{CC}



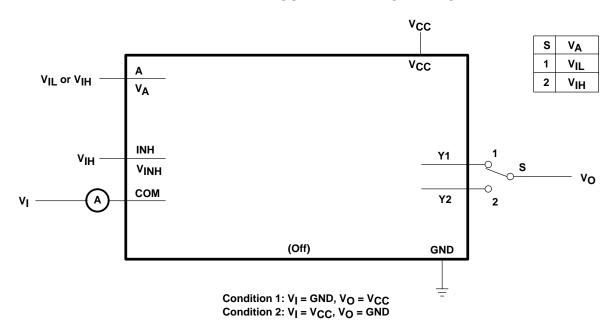


Figure 3. Off-State Switch Leakage-Current Test Circuit

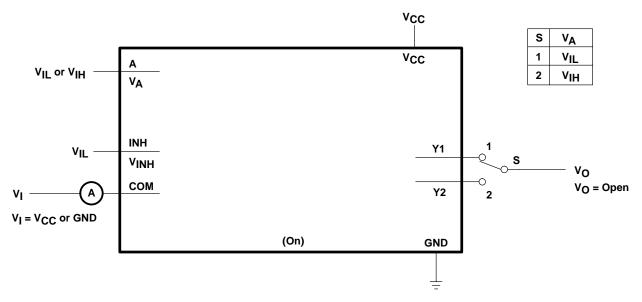
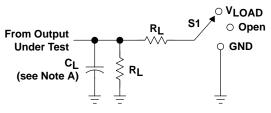


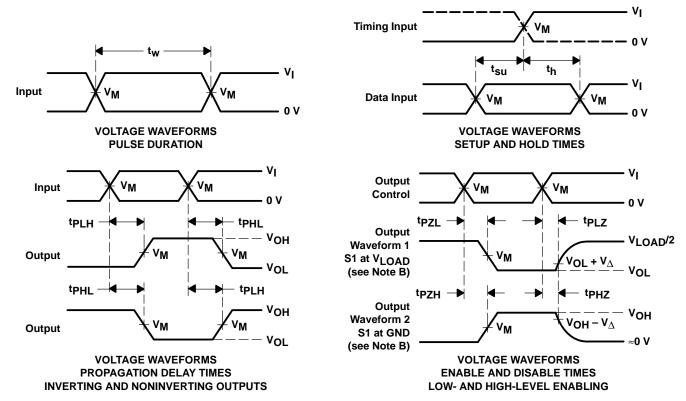
Figure 4. On-State Switch Leakage-Current Test Circuit



TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	VLOAD
tPHZ/tPZH	GND

LOAD	CIRCU	JIT
------	-------	-----

.,	INF	PUTS	.,			_	.,
VCC	٧ _I	t _r /t _f	VM	VLOAD	CL	RL	$v_{\scriptscriptstyle\Delta}$
1.8 V \pm 0.15 V	VCC	≤2 ns	V _{CC} /2	2×VCC	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	VCC	≤2 ns	V _{CC} /2	2×VCC	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	VCC	≤2.5 ns	V _{CC} /2	2×VCC	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	VCC	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_{O} = 50 \Omega$.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms



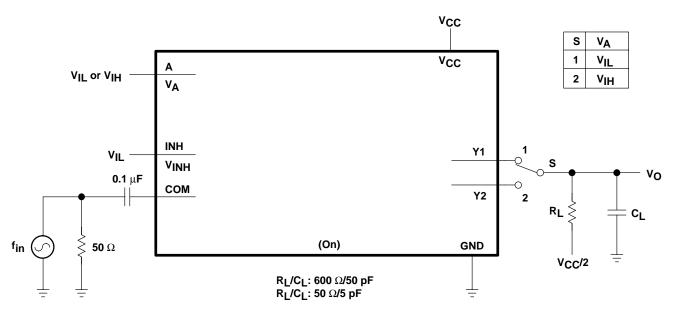


Figure 6. Frequency Response (Switch On)

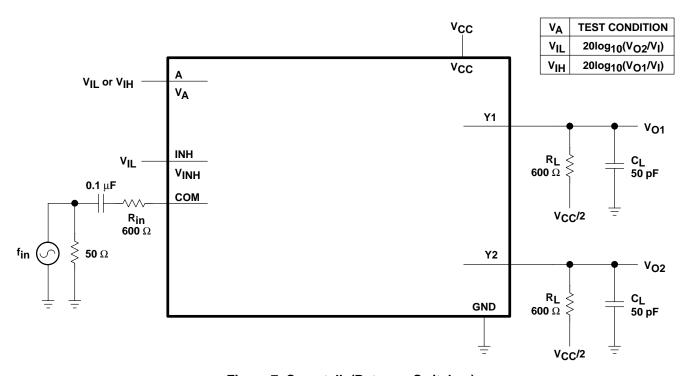


Figure 7. Crosstalk (Between Switches)

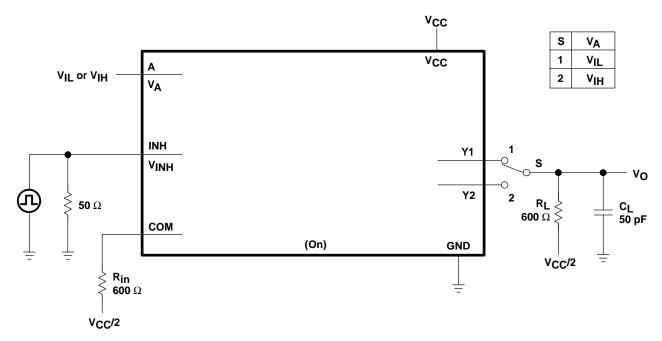


Figure 8. Crosstalk (Control Input, Switch Output)

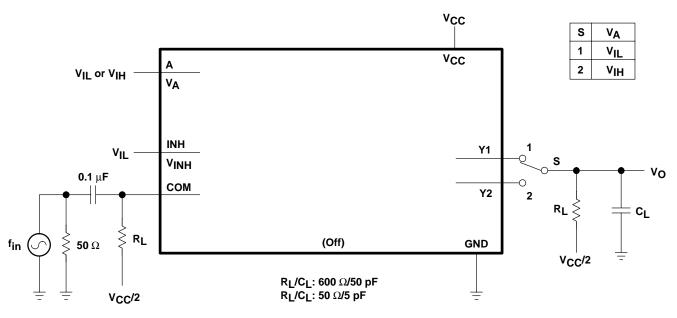


Figure 9. Feed Through (Switch Off)

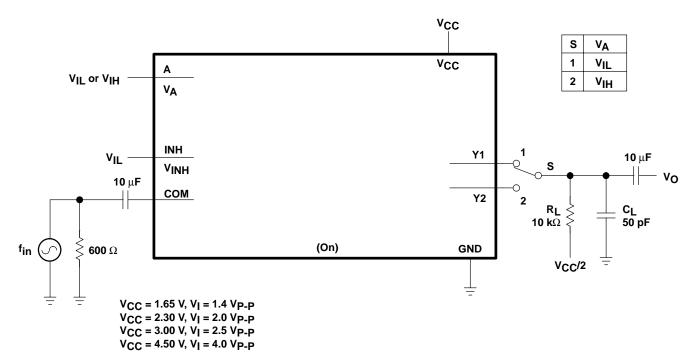
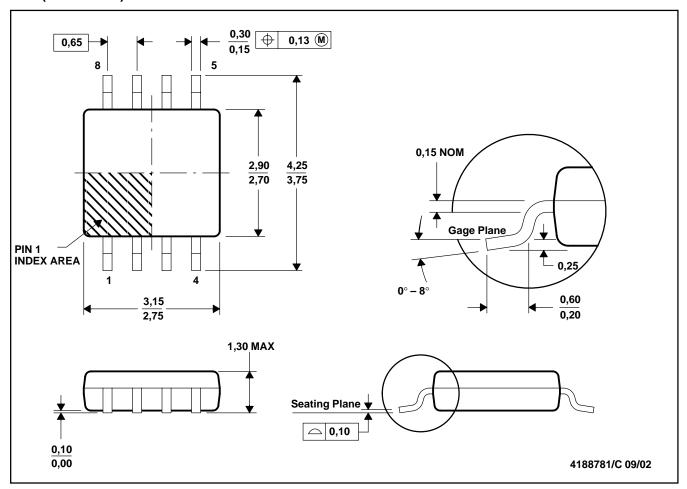


Figure 10. Sine-Wave Distortion

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

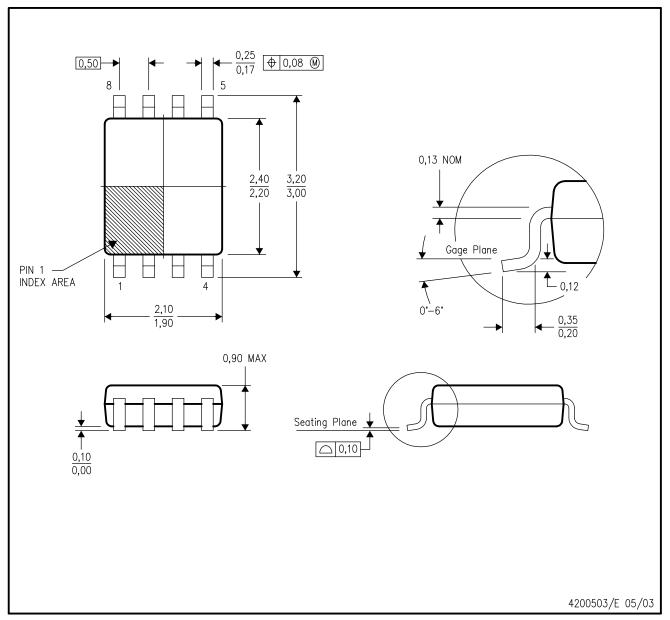


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

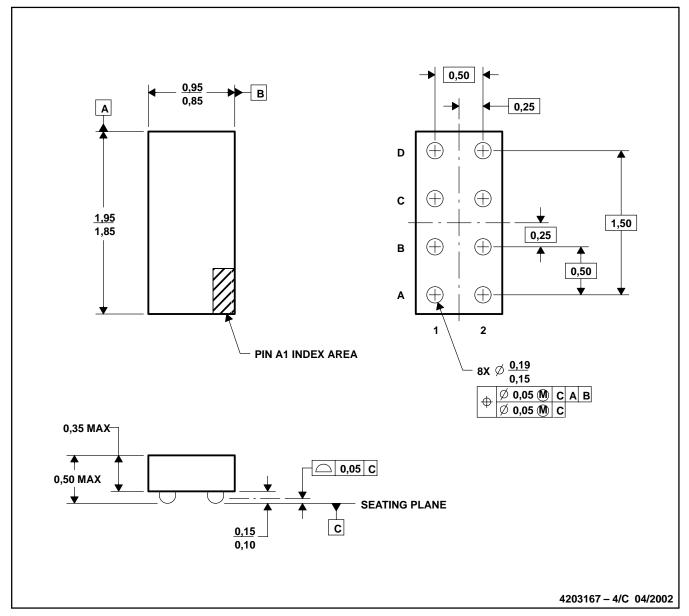
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation CA.



1

YEA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY

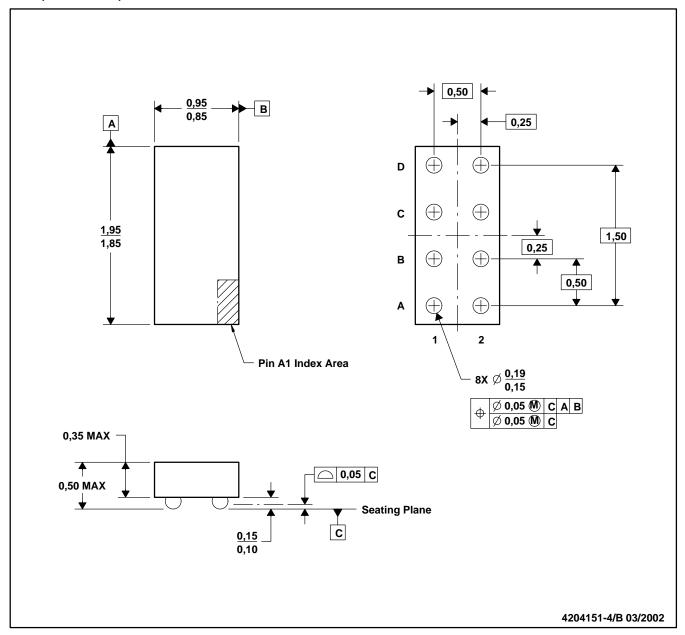


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.

YZA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



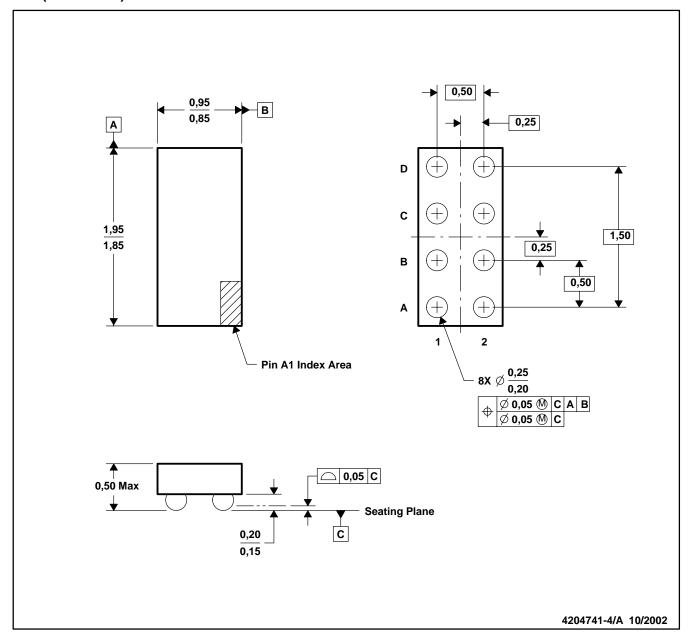
- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. Package complies to JEDEC MO-211 variation EB.
 - E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



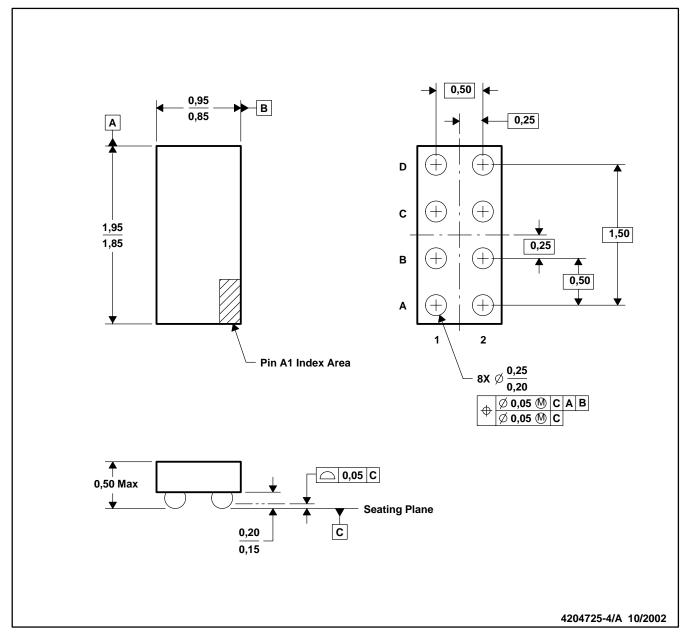
- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 420741) for lead-free.

NanoFree is a trademark of Texas Instruments.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third—party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Mailing Address:

Texas Instruments Post Office Box 655303 Dallas, Texas 75265

Copyright © 2003, Texas Instruments Incorporated